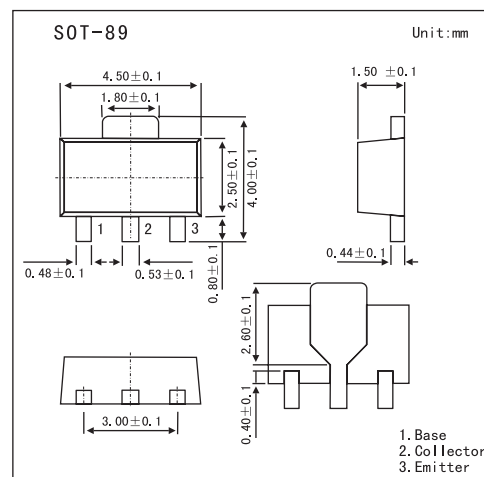


Small Signal Transistor

2SC5211

■ Features

- High voltage $V_{CE0}=50V$.
- Small package for mounting.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	55	V
Emitter-base voltage	V_{EB0}	4	V
Collector-emitter voltage	V_{CE0}	50	V
Peak collector current	I_{CM}	600	mA
Collector current	I_C	400	mA
Collector dissipation	P_C	500	mW
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=10\mu A, I_E=0$	55			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E=10\mu A, I_C=0$	4			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C=100\mu A, R_{BE}=\infty$	50			V
Collector cutoff current	I_{CBO}	$V_{CB}=25V, I_E=0$			1	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=2V, I_C=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=4V, I_C=100mA$	90		500	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=10mA$		0.15	0.5	V
Gain bandwidth product	f_T	$V_{CE}=6V, I_E=-10mA$		150		MHz

■ h_{FE} Classification

Marking	TD	TE	TF
h_{FE}	90~180	150~300	250~500